Quad 2-Input NAND Gate

The MC74VHCT00A is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT00A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT00A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC}=0\ V$. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 5.0 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 3.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

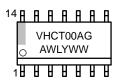


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MARKING DIAGRAMS







TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 6 of this data sheet.

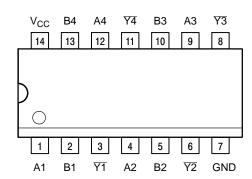


Figure 1. Pin Assignment (Top View)

PIN ASSIGNMENT					
1	IN A1				
2	IN B1				
3	OUT \(\overline{\gamma} \)				
4	IN A2				
5	IN B2				
6	OUT Y2				
7	GND				
8	OUT \(\overline{73} \)				
9	IN A3				
10	IN B3				
11	OUT Y4				
12	IN A4				
13	IN B4				
14	V _{CC}				

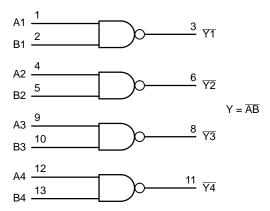


Figure 2. Logic Diagram

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	Н
L	н н	Н
Н	L	Н
Н	Н	L

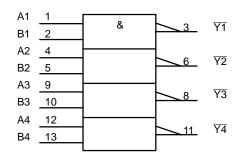


Figure 3. IEC LOGIC DIAGRAM

MAXIMUM RATINGS

Symbol	Ch	aracteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	$V_{CC} = 0$ High or Low State	-0.5 to 7.0 -0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current	$V_{OUT} < GND; V_{OUT} > V_{CC}$	+20	mA
I _{OUT}	DC Output Current, per Pin		+25	mA
I _{CC}	DC Supply Current, V _{CC} and	GND	+50	mA
P_D	Power Dissipation in Still Air,	SOIC Package (Note 1) TSSOP Package (Note 1)	500 450	mW
TL	Lead temperature, 1 mm from	n case for 10 s	260	°C
T _{stg}	Storage temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 > 3000	V
I _{Latch-Up}	Latch-Up Performance (Note 5)	Above V _{CC} and Below GND at 125°C	±300	mA

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) $\leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Derating -
- SOIC Package: -7 mW/°C from 65° to 125°C
 TSSOP Package: -6.1 mW/°C from 65° to 125°C
- 2. Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characte	ristics	Min	Max	Unit
V _{CC}	DC Supply Voltage		3.0	5.5	V
V _{IN}	DC Input Voltage		0.0	5.5	V
V _{OUT}	DC Output Voltage	VCC = 0 High or Low State	0.0 0.0	5.5 V _{CC}	V
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

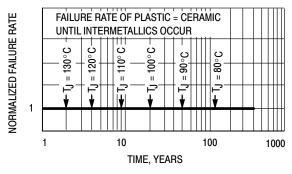


Figure 4. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	7	Γ _A = 25°(3	T _A ≤	85°C	T _A ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		٧
	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS $C_{load} = 50 \ pF$, Input $t_r = t_f = 3.0 \ ns$

				T _A = 25°C		C	T _A ≤	. 85°C T _A ≤ 125°C		125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , Maximum Propogation Delay, Input A or B to Y	Propogation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.1 5.5	10.0 13.5		11.0 15.0		13.0 17.5	ns
	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.1 3.6	6.9 7.9		8.0 9.0		9.5 10.5		
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 6)	17	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

$\textbf{NOISE CHARACTERISTICS} \text{ (Input } t_{\text{r}} = t_{\text{f}} = 3.0 \text{ns, } C_{\text{L}} = 50 \text{pF, } V_{\text{CC}} = 5.0 \text{V, Measured in SO Package)}$

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.4	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.4	- 0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

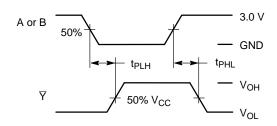


Figure 5. Switching Waveforms

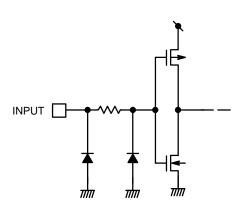
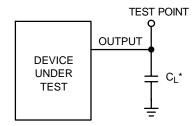


Figure 7. Input Equivalent Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

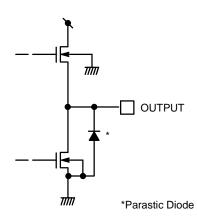


Figure 8. Output Equivalent Circuit

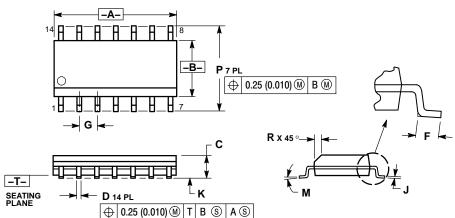
ORDERING INFORMATION

Device	Package	Shipping [†]	
MC74VHCT00ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel	
MC74VHCT00ADTR2G	TSSOP-14	2000 / Tong & Book	
NLV74VHCT00ADTR2G*	(Pb-Free)	2000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

PACKAGE DIMENSIONS

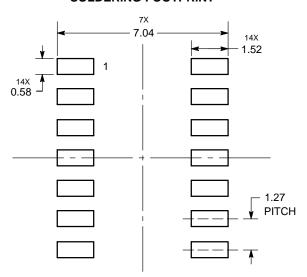
SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

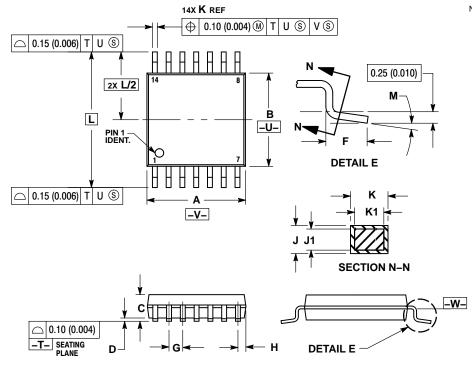
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

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PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
 - 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 - EXCEED 0.15 (0.006) PER SIDE.

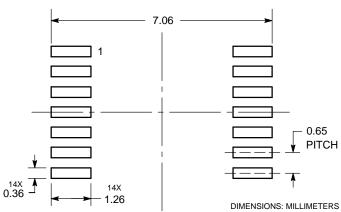
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR DEOTELISCON ALL
 - DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 5. TERMINAL NUMBERS ARE SHOWN FOR
 - REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE

DETERMINED AT DATUM PLANE -W						
	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.90	5.10	0.193	0.200		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65	BSC	0.026	BSC		
Н	0.50	0.60	0.020	0.024		
J	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40	BSC	0.252	BSC		
М	0°	8 °	0°	8 °		

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